## MAR 0 5 2007 OFFICE OF PETITIONS

## EXHIBIT A

U.S. SERIAL NO.: 10/521,619

## ASSIGNMENT OF PATENTS

This Assignment of Patents (this "Assignment") is effective as of the Initial Closing Date (as defined in the Asset Purchase Agreement (the "Asset Purchase Agreement"), dated as of October 10, 2003, by and among ASML Holding N.V., a Dutch company ("Parent"), ASML U.S., Inc., a Delaware corporation and a wholly-owned subsidiary of Parent ("Seller U.S."), and the other affiliates of Seller U.S. party thereto (together with all of the foregoing parties, each a "Seller" and collectively the "Sellers"), on the one hand, and Thermal Acquisition Corp., a Delaware corporation ("Buyer")). Capitalized terms used herein but not defined shall have the meanings ascribed to such terms in the Asset Purchase Agreement.

WHEREAS, upon the terms and subject to the conditions in the Asset Purchase Agreement, Sellers have agreed to assign and transfer to Buyer, among other things, certain Patents (as defined below);

WHERRAS, in order to further effect the assignment and transfer of such Patents, Buyer has requested that Seller U.S. execute and deliver to Buyer this Assignment;

NOW, THEREFORE, for good and valuable consideration, the receipt and sufficiency of which is hereby acknowledged:

1. Sellers agree to and hereby do assign, sell, transfer, grant and convey to Buyer, its successors and assigns, all of Sellers' worldwide right, title and interest in and to all Patents listed on schedule 3.18(a)(i) of the Disclosure Schedule and all causes of action, demands, judgments, claims, or other similar rights of Sellers relating primarily to such Patents.

"Patents" shall mean all U.S. and foreign patents and applications therefor and all reissues, divisions, renewals, extensions, provisionals, continuations and continuations-in-part thereof.

- 2. Sellers authorize and request the United States Patent and Trademark Office and head of any foreign patent office to issue all patent registrations which may issue on any applications for any Patents to Buyer, its successors and assigns, in accordance with this Assignment.
- 3. Promptly upon the request of Buyer, Sellers shall execute such documents and perform such actions as may be necessary to perfect the assignment of rights contained in this Assignment.
- 4. Nothing herein shall affect, or be deemed to affect, the representations, warranties, covenants, and indemnities contained in the Asset Purchase Agreement.
- 5. This Assignment may be executed in one or more counterparts and signature may be delivered by facsimile, each of which shall be deemed an original, but all of which together shall constitute one and the same instrument.

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IN WITNESS WHEREOF, Seller U.S. has caused this instrument to be executed by its duly authorized corporate officer as of the Closing Date.

ASML U.S., Inc.

Ву: .

Name: C. Douglas Marsh

Title: Vice President Business Integration

& U.S. Institutional Relations

ACKNOWLEDGED AND AGREED:

Thermal Acquisition Corp., a Delaware Corporation

By:

Name: Jerauld Cutini

Title: President and Chief Executive Officer

IN WITNESS WHEREOF, Seller U.S. has caused this instrument to be executed by its duly authorized corporate officer as of the Closing Date.

ASML U.S., Inc.

By:

Name: C. Douglas Marsh

Title: Vice President Business Integration & U.S. Institutional Relations

ACKNOWLEDGED AND AGREED:

Thermal Acquisition Corp., a Delaware Corporation

Name: Jerauld Cutini

Title: President and Chief Executive Officer

## DISCLOSURE SCHEDULES

**SCHEDULE 3.18(a)(i)** 

The following Patents:

RECEIVED

MAR 0 5 2007

OFFICE OF PETITIONS

Attachment 1 to Disclosure Schedule 3.18(a)(I)

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1		ı		Title/Inventors	Cont. Tax.		
✓	16178		£ 1		Miling Data	Patent No.	Foreign
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FA ·	16178	ė į	A-T-	LOW TEMPERATURE CHEMICAL VAPOR	06/29/87	07/04/89	
4	16178	7	AST	CVD REACTOR AND GAS DIFFERENCE FILMS	06/14/86	12/26/97	Japan
FA	16178	7-JP	AT	CVD PEACTOR AND CLEE	07/044,326 10/27/87	4,834,022	-
			· :	CALL MEALLUK AND GAS INJECTION SYSTEM	61-165449	2076449	
∢	16178	8	AT	FLUIDIZED BED HEATER FOR SHARCONDITIONS	07/14/86	96/60/80	usder
_	Amarc	I		PROCESSING	707262	4,673,799	
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₹	44153	7	AJŢ	TRIAL ROBOT FOR USB IN CLEAN ROOM	07/080 401	- 1	
¥	44521	Ť	¥4		08/26/87	4,787,813, 11/29/88 Abandoned	Expired
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			į	RAGE	07/214,909	4,891,247	
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	Patent No./	Issue Date	Abandoned			Abendoned in favor	(A-47444-1)	Abandoned	Abandoned	Abandoned		2222416/	Abendoned				Abendoned in favor	(A-4744-2)	Abandoned in favor	(A-47444-3)	Abandoned per client hr 09/14/98	5,088,773	62/18/92 5 136 076	08/11/92	5,113,789
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	Title/Inventors	BOROSILICATE GLASS FILMS FOR MIT THE EVITE	METALLIZATION STRUCTURES IN SEMICONDICTOR PROGRAMMENT	METHOD FOR IMPROVING THE STEP COVERAGE	CHEMICAL VAPOR DEPOSITION	SILANE/Grainski	CHEMICAL VAPOR DEPOSITION USING DIST ANE/	CHEMICAL VAPOR DEPOSITION FISHED BY	Gradenski	Grainaid VAPOR DEPOSITION USING DISILANE	PROCESSES USING DISILANE (Gralman)	Turner	CHEMICAL VAPOR DEPOSITION TISING DIVER	SILANE/Gralenski	CHEMICAL VAPOR DEPOSITION USING DYED SILANE/GRIDAL	CHEMICAL VAPOR DEPOSITION LISTING DISTI AND	Gralenski	CHEMICAL VAPOR DEPOSITION ISSNIG PICT ASST	Gralenski	CHEMICAL VAPOR DEPOSITION USING DISTI AND!	HI BCTRICALLY INSTITATED PRING COMME	APPARATUS/Gralenski	INIECTOR AND METHOD FOR DELIVERING GASBOUS CHEMICALS TO A STREET		
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Reference No.					•	· .
		-	Title/Inventors	Serial No./	Patrat No./	Possid:
		WSG		Filing Date	Isme Date	Countries
52354	ğ	A-T-WSG	SHIP CLEANING FLOW CONTROL ORIFICE/Kamian	04/24/90	05/19/92	
52354	<u>e</u>	AJT	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	09/18/90 2-216935	01/13/99	South Korea
52354	₽.	ASG WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	08/17/90	09/03/99	Japan
52354	DB:	AJT WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	90307398.9	02/14/92	Taiwan .
52354	B	A5T WSG	SELP CLEANING FLOW CONTROL ORIFICE/Kamian	90307398.9	02/15/95 457670 (07/15/05	Germany
52354	禹	A-T-WSG	SELP CLEANING FLOW CONTROL ORIFICE/Kamian	90307398.9	Abandoned	open.
52354	₩	ASG		07/06/90	02/15/95 457/570	France
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<del></del>	F	AJT		07/06/90	4556/9 02/15/95 Abandoned	Belgium
		WSG	CONTROL OXIFICE/Kamian	903 <b>07</b> 398.9 07/06/90	453 <i>6</i> 79 02/15/95	Switzerland
	à	AJT WSG	SELP CLEANING FLOW CONTROL ORIFICE/Kemien 9	90307398.9	Abandoned5/24/02	ļ
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IN	33		_		433679 02/15/95	Netherlands
		1		07/06/90	453679	Sweden

Reference No.			Title/Inventure	.		٠	
L.				Serial No./ Filing Date	Pertent No./	Foreign	_
쁘	DK DK	44	SELP CI RANING PLOTIT CO. TITLE		Abendoned	Countries	
		WSG	CONTROL ORIFICE/Kemien	90307398.9 07/06/90	453679 02/15/95	Denmark	
¥	AT	AT.	SELP. CLEANING PLOW. CONTROL ORIFICE/Remiss		Abendoned	•	
!				07/06/90	453679	Austria	
		を見る	U-SHAPED HEATER LINES/Walker	07/601,261	Abandoned		
瓦		15	U-SHAPED HEATER LINES/Walter	10/22/90	08/19/92	•	
2		₹ <del>7</del>		10/22/91	Abendoned 08/19/92	South Korea	•
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<u>.   </u>		158		9130 <del>9</del> 735.8' 10/22/91	Abandoned	Вшоре	
P		ATT	E. SOURCE BUBBLEK/Richie	07/601,270	5,078,922		
[5	$\exists$	;		3-274069	1929857	Japan	
ž		MSS	LIQUID SOURCE BUBBLER/Richie	18592/91	191851		
出		AST	LIQUID SOURCE BUBBLER/Richie	10/22/91	01/27/99	South Korea	•
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i	+	AST	LIQUID LEVEL SENSOR ASSEMBLY/Goodrich	02/201			
2	14	ATT		10/23/90	5,029,471 07/09/91		•
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Title/Inventors	VAPOR DELIVERY SYSTEM	CHEMICAL REFILL SYSTEM	HEATER FOR PROCESSING OASTES	Supplied Charles Collins	GAS HEATER FOR PROCESSING GASES/Colling	CAN TIPARTOR TO A SECOND SANDARD	CASSING GASES/Colins	GAS HRATER FOR PROCESSING GASES/Colling		GAS HEATER FOR PROCESSING GASES/Colling		GAS HEATHER BOD BID CONTRACTOR	CASES/Colling	GAS HRATER FOR PROCESSING GASBSIO-11:	Smile County County	GAS HEATER FOR PROCESSING GASES/Colling	OAN UTTER BOX SAN	CAST ARALIER FOR PROCESSING GASES/Collins	GAS HEATER BOD BROCESSEIG COMME	A CASHES/Collins	BPSG STABILITY. ENHANCING CAP LAYER/	OZONE PRETREATMENT FOR IMPROVED 177	RESISTANCE/Curtis	CHEMICAL VAPOR DEPOSITION OF SILICON	DIOXIDE USING HEXAMETHYLDISH AZANE/Kn	CHEMICAL VAPOR DEPOSITION OF STITES	DIOXIDE FROM HEXAMETHYLDISILAZANE AND OZONBYOXYGENKAREII	
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6				METHOD/Hands	08/191,091	Abendoned	Est manage	
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4	59072		124	METHOD OF MANTHACTHERICS	02/04/94	Destruction	To	
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瓧	59072	<u>Σ</u>	AT	METHOD OF MANUFACTURING A GLASS	DCT//1004/01000	(A-59072-1)		•
4	59072	-	154	METHOD OF MANTER ATTENDED	02/04/94	Abandoned	PCT	T .
<b>▼</b>	Ser.		MSS	SUBSTRATE FOR A THIN FILM/Harda	08/542,279 10/12/85	Abendoned		
<u>:                                    </u>	3		MSS	METHOD OF MANUFACTURING SIDE WALLS AND	08/237,691	Abandoned in farmer		$\exists$
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4	59073		57	ON ON WANTED COMPANY	•			·
	<i>:</i>	•	MSS	CONDUCTOR DEVICE HAVING SIDE WALLS.	08/512,346/ 08/08/95	Abendon		T
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∢	59425		AJT	PRECTIPION TO	Filed 05/04/94		<u>,</u>	<u> </u>
<	50471	1		ž.	Closed			T
		<del></del> -	MSS	DELIVERING GASES TO A SURFACE/Dedominey	08/276,815 07/18/94	Abandoned in favor		
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T				OR DELIVERING GASES		190355	South Kores	-
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			7	URFACE/Dedontney	-	F69513104.4 11/03/99	Germany	

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¥.	59471	4	15	SINGLE BODY INTECTOR AND PERSON	07/10/98	Closed	FCT	T
Y.	59471	4年	MSS	CHAMBERAGIIC, et al.	98807203.3 07/10/98		China	<del>-</del> T -
			MESS	CHAMBER; Adam O. Miller, Deniel M. D. St.	00108287.5			
<u>₩</u>	59471	4-JP	ATA MSS	SINGLE BODY INTECTOR AND DEPOSITION	12/21/00			
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j		$\neg$	MSS	CHAMBERAMIE, et al.	2000-7000430	355058	South Pones	
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毘	58471	4	15	SINGI B BODY BY	07/10/98	03/04/02	Singapore	
	_		MESS	CHAMBERAGILE, et al.	98933329.9		Ruman	
₹	<u> </u>	5	AT	SINGLE BODY INTECTION AND PERSON	07/10/98	•	R. Company	
····	<u> </u>		MSS PAR	CHAMBER/Miller, Dobbin	09/757,542 01/09/01	6,521,048		
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4	50164	1	A TT	· Constant	09/113,823 07/10/98			
			MSS	MATERIAL Pro Timple: I LANAR LAYER OF	08/447,809	5.668.063		
FA	60164	鼠	AT	METHOD OF PLANARIZING A LAYER OF	05/23/95	09/16/97		
FA	60164	P.	ATT	MATERIAL Pry, Lightfoot, Lomond METHOD OF PT ANA PITTING	05/06/96		South Korea	
臣	60164	£	MSS	MATERIAL Pry, Lightfoot, Lomond	8-535689 05/06/96		Japan	
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V	62201	+			2		PCT	
4	62733	7		C. A. CVD OALDE FILMS/R.y.	08/704,227 08/77/94	5,786,278		
	75130	4	AT.	MITROGEN SHIELD/Van Tran	9	7//28/98		
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<b>∢</b>	62732	1	5 夏	PROTECTIVE GAS SHIELD FOR CHEMICAL VAPOR		(A-62732-1) 5.944.900		
A	62732	7	15 1	FOR CHEMICAL VAPOR	11/24/97	08/31/99		
	K378A	1	January 1	DEPOSITION APPARATUS			· .	
	3		MSS	METHOD OF FORMING DIELECTRIC FILMS WITH REDUCED METAL CONTAMINATION Caivalbeira	08/573,318 12/15/95	Abandoned in favor of 08/599,092		- 1
¥	98/29	_	45	1		(A-62786-1)		
			WES .	REDUCED METAL CONTAMINATION/Cervalheira	02/07/96 02/07/96 CIP: of 08/573.318	Abandoned		1
FA	98/239	<u>-</u>	15	- 1	Filed 12/15/95			
FA	62786	<u>a</u>	MSS		96198872.X 12/11/96		China	1
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			WESS.	THOD OF FORMING DIELECTRIC FILMS WITH DUCKED METAL CONTAMINATIONS	85109526	088844	Taiwan	
閏.	62786	1-EP	AJT.	-	08/06/96 96943723.5	12/13/97		
毘	98/239	1.联		HOD OF FORMING DISLECTRIC FILMS WITH	12/11/96	Abendan	carope	
£;	62786	24		HOD OF FORMING DIELECTRIC FILMS WITH	02/08/99 PCI/US96/19819		Hong Kong	. 1
	62998			ECTRIC PLANARIZATION TECHNIQUE WITH	12/11/96		2	
-	20059			METHOD OF IMPROVING DEPOSITION THICKNESS				
<u> </u>	80069	1	T	MIZING OF SIO2 FILM CONROBMAT THE THE				· ·
			7	OSPHERIC PRESSURE CHEMICAL VAPOR	08/801,997	5,855,957		T-

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STRING   S	TW.   ATT   COTTAMEZANG DEPOSITION   CONFORMALITY IN   STOLES   CONTAMEZANG DEPOSITION   CONFORMALITY IN   CONTAMEZANG DEPOSITION   CONTAMEZANG DEPOSITION   CONFORMALITY IN   CONFORMALITY								
TEM	Secondary   Seco					£10100AUT ATTIT	Serfal No.	Patent No./	Parefen
ATT   OFTIMETION OF SIGN FILM CONFORMALITY IN   STOLESAS   107673   107674   10767	GOING   TW   ALT   OFTINATIVO STILAT CONFORMALITY IN   GYILLESS   107679   Taiwood   GOING	-			JEM	DRPOSTITON	Filing Date	Issue Date	Countries
TEACHGA TO OFT IMALIANG SIOUS FILM CONFORMALITY IN   \$7012245   107673     AT	G2008 PC   AT   OPTIMIZATION OF SIGN FILM CONFORMALITY IN PROPERS   1076730   Tainway	Τ	3008	P	H.V		76/81/20	01/05/99	
ATT	Garder   Att   Coptimization of Biological Activities   Coptimization of Bio				IEW	UP I IMIZING SIO2 FILM CONFORMALITY IN TROSAS APCVD	87012245	107673	Taiwan
IRM	SEASON   ALT   AMERINDO PROPERTIES FREE STATES   PARTICION   PAR			<b>%</b>	\ <u>^</u>	OPTIMIZATION OF SIC? FIT M CONBOBYAT THE FL	86/81/70	02/02/00	
AJT         LOW K DIELECTRICS PREPARED FROM         08/679 &44         5.92,420           MSS         CROSS-LINKED PEXS (CL.PPXS)/Lo.         07/1699         07/1699         07/1699           MSS         DIEL BCTRICLe.         07/1497         Abendomod.         07/1497         Abendomod.           ATT         A METHOD OF PLANARIZING A DIELECTRIC         Closed         Closed         Abendomod.           AST         LAVER WITH REDUCED HYDROGEN DIFFUSION         Enda         1.000         Abendomod.           AST         LOW K DIELECTRICS PREPARED FROM PECVID         Enda         1.000         5.976,238           AST         LOW K DIELECTRICS PREPARED FROM PECVID         Enda         1.000         5.976,238           AST         LOW K DIELECTRICS PREPARED FROM PECVID         Enda         1.000         5.976,238           AST         HIGH TEAPERATURE ROLLER MODULEKIRIng         0.0019,349         5.976,238         1.102,99           AST         HIGH TEAPERATURE ROLLER MODULEKIRING         Closed         1.000         1.000         1.000           AST         HIGH TEAPERATURE ROLLER MODULEKIRING         Closed         1.000         1.000         1.000           AST         METHOD OF CONTAMINATION REDUCTION BY         0.001060693         Abendomed         1.000     <	G2265   AJT   LOW K DIELECTRICS PREPARED FROM   016679,864   5,925,420   071,059   0		• .		MESS	ATMOSTHERIC PRESSURE CHEMICAL VAPOR	PCI/US98/02842 02/17/98	Absordoned	PCT
MSS   CROSS-LINEED PPXS (CL.PYXS)Less   UR6079, 864   5505420     AJT   CROSSLINEED AROMATIC POLYMERS SA LOW   PCITUSS7110575   Absadoned     AND THE SCTRICT.Les   AMERICAN OF PLANARIZING A DIRECTRIC Closed     AND THE SCTRICT REPAIRED FROM PECVD   Eloid     AND PROTOUR STREATH REDUCED BYDROGEN DIFFUSION   Eloid     AND PROTOUR STREATH REDUCTION BY   GAZ3,635     AND PROTOUR STREATH STREATH STREATH   Eloid     AND PROTOUR STREATH STREATH STREATH   Eloid     ANT METHOD OF CONTAMINATION REDUCTION BY   GAZ3,635     ANT METHOD OF CONTAMINATION REDUCTION BY   GAZ3,667     ANT METHOD OF CONTAMINATION REDUCTION BY     ANT METHOD OF CONTAMINATION REDUCTION BY     ANT METHOD OF C	MASS   CROSS-LINCED PFXS (CL.PTXS)/Lo.   U0016/96   5925,420   63265   PCT		3265		2	LOW K DIRLECTRICS PREPARED PROM			
AT	Colored   AJT   CROSSILNEED AROMATIC POLYMERS SALOW   CHICAGO	7	_		MSS	CROSS-LINKED PPXS (CL. PPXS)/L&	U&/679,864 ·	5,925,420	
AMETHOD OF FLANARIZING A DIELECTRIC   U1/14/97	ATT		_	ည် ည	AST. MSS.	CROSSLINKED AROMATIC POLYMERS SA LOW E. DIELECTRICA	PCT/US97/10575	O//20/99 Abandoned	PCI
AJT         LOW EDIELSCTRICS PREPARED FROM PECVD         Hold           ASS         AND PECVD OF SELECTED SILOXANESSLee         69/019,349         5,576,258           AJT         HIGH TEMPERATURE ROLLER MODYLEKIeiner.         09/019,349         1,029           AJT         METHOD FOR FORMING VERTICALLY EXTENDED Closed         11,02/99           AJT         METHOD FOR FORMING VERTICALLY EXTENDED Closed         1,02/99           AJT         METHOD OF CONTAMINATION REDUCTION BY Closed         08/02/99           AJT         METHOD OF CONTAMINATION REDUCTION BY CONMANDATION REDUCTION BY CONCAMINATION REDUCTION BY CONCESSED SURFACE CONTAMINATION REDUCTION BY CONCESSED SURFACE CONTAMINATION REDUCTION BY C	G3659   AJT   LOW F DIELECTRICS PREPARED FROM FECVD   Hold		33.47		AJT MSS	A METHOD OF PLANARIZING A DIRLECTRIC LAYER WITH REDUCED HYDROGEN DIFFUSION/	Closed		
AND PECYD OF SELECTED SILOXANESL.co	MASS	T	3579		A TT				
HIGH TEMPERATURE ROLLER MODULE/Kleiner   09/019,349   5,976,258     AIT	Secondary   Alt				MSS	AND PECYD OF SET ECTED SILOXANES/Lee	Hold		
AJT         METHOD FOR FORMING VERTICALLY EXTENDED         UANDARS         11/02/99           MSS         RABERDDED LOW, K. MATERIALS/Fry         Closed         11/02/99           AJT         OPTIMIZATION OF SIO, FILM CONFORMITY         Closed         66/29/99           AJT         MBTHOD, OF CONTAMINATION REDUCTION BY         08/023,635         5,916,378           AJT         MBTHOD OF CONTAMINATION REDUCTION BY         98804123.5         66/29/99           AJT         MBTHOD OF CONTAMINATION REDUCTION BY         09/06/98         Abandoned           AJT         METHOD OF CONTAMINATION REDUCTION BY         09/26/00         Abandoned           AJT         METHOD OF CONTAMINATION REDUCTION BY         09/26/00         09/26/00           AJT         METHOD OF CONTAMINATION REDUCTION BY         03/106/98         10-539667           AMS         FORMATION OF ALL OXIDE SURFACE         03/106/98         03/106/98	AJT   METHOD FOR FORMANG VERTICALLY EXTENDED   U205598   11/0299	상	9		A PER	HIGH TEMPERATURE ROLLER MODULB/Kleiner	09/019,349	5,976,258	
AJT         OPTIMIZATION OF SiO, FILM CONFORMITY         Closed           AJT         METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE         08/823,635         5,916,378           AJT         METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE         98804123.5         06/29/99           AJT         METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE         09/26/00         Absandoned           AJT         METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE         09/26/00         09/26/00           AJT         METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE         09/26/00         09/26/00           AJT         METHOD OF CONTAMINATION REDUCTION BY GALLOSSEE         09/26/00         09/26/00           AJT         METHOD OF CONTAMINATION REDUCTION BY GALLOSSEE         09/26/00           AJT         METHOD OF CONTAMINATION REDUCTION BY GALLOSSEE         09/26/00	G3662   AJT   OPTIMIZATION OF SIO, FILM CONFORMITY   Closed	<u>8</u>	1999		ASS	X EXTENDED	UZ/05/98 Closed	11/02/99	
AT         METHOD OF CONTAMINATION REDUCTION BY.         08/823,635         5,916,378           AS         FORMATION OF ALL OXIDE SURFACE         03/11/97         06/29/99           AJT         METHOD OF CONTAMINATION REDUCTION BY         98804123.5         5,916,378           AJT         METHOD OF CONTAMINATION REDUCTION BY         98804123.5         05/29/99           AJT         METHOD OF CONTAMINATION REDUCTION BY         00106069.3         Abandoned           AJT         METHOD OF CONTAMINATION REDUCTION BY         10-539667         Abandoned           AJT         METHOD OF CONTAMINATION REDUCTION BY         10-539667         03/106/98           AJT         METHOD OF CONTAMINATION REDUCTION BY         10-539667         03/106/98           AJT         METHOD OF CONTAMINATION REDUCTION BY         10-539667         03/106/98           AJT         METHOD OF CONTAMINATION REDUCTION BY         99-7008224         03/106/98	Corporation of Sucy Fill Conformation of S	13	238	T	<b>A</b> 54		٠		<u> </u>
AJT         METHOD OF CONTAMINATION REDUCTION BY.         08/823,655         5,916,378           MSS         FORMATION OF ALL OXIDE SURFACE         03/11/97         06/29/99           AJT         METHOD OF CONTAMINATION REDUCTION BY         98804123.5         06/29/99           AJT         METHOD OF CONTAMINATION REDUCTION BY         00106069.3         Abendoned           AJT         METHOD OF CONTAMINATION REDUCTION BY         09/26/00         10-539667           AJT         METHOD OF CONTAMINATION REDUCTION BY         10-539667         03/106/98           AJT         METHOD OF CONTAMINATION REDUCTION BY         10-539667         03/106/98           AJT         METHOD OF CONTAMINATION REDUCTION BY         10-539667         03/106/98           AJT         METHOD OF CONTAMINATION REDUCTION BY         99-7008224         99-7008224	AJT   METHOD-OF CONTAMINATION BY   08/823,655   5916,378						Closed		
MES         FORMATION OF ALL OXIDE SURFACE         08/823,655         5,916,378           AJT         METHOD OF CONTAMINATION REDUCTION BY         98804123.5         06/29/99           AJT         METHOD OF CONTAMINATION REDUCTION BY         98804123.5         06/29/99           AJT         METHOD OF CONTAMINATION REDUCTION BY         00106069.3         Abendoned           AJT         METHOD OF CONTAMINATION REDUCTION BY         09/26/00         10-539667           AJT         METHOD OF CONTAMINATION REDUCTION BY         10-539667         03/106/98           AJT         METHOD OF CONTAMINATION REDUCTION BY         10-539667         03/106/98           AJT         METHOD OF CONTAMINATION REDUCTION BY         10-539667         03/106/98           AJT         METHOD OF CONTAMINATION REDUCTION BY         99-7008224         99-7008224	G3665         CN         AJT         METHOD OF CONTAMINATION REDUCTION BY METHOD OF CONTAMINATION BY METHOD OF		599		15			·	:
MSS FORMATION OF ALL OXIDE SURFACE 03/06/98  LAYERS/Bailey, Brady.  MSS FORMATION OF ALL OXIDE SURFACE 03/06/98  LAYERS/Bailey, Brady.  AJT METHOD OF CONTAMINATION REDUCTION BY 09/26/00.  LAYERS/Bailey, Brady.  MSS FORMATION OF ALL OXIDE SURFACE 09/26/00.  LAYERS/Bailey, Brady.  MSS FORMATION OF ALL OXIDE SURFACE 03/106/98  LAYERS/Bailey, Brady.  AJT METHOD OF CONTAMINATION REDUCTION BY 99-7008224	G3665         CN         AJT         MBTHOD OF CONTAMINATION REDUCTION BY         98804123.5         Chima           G3665         HK         AJT         METHOD OF CONTAMINATION REDUCTION BY         00106069.3         Abandoned         Earg K           G3665         HK         AJT         METHOD OF CONTAMINATION REDUCTION BY         0012600.         Abandoned         Earg K           G3665         JP         AJT         METHOD OF CONTAMINATION REDUCTION BY         10-539667         Japan           G4665         KR         AJT         METHOD OF CONTAMINATION REDUCTION BY         99-7006224         South K           G58 (463035-828)         AJT         METHOD OF CONTAMINATION REDUCTION BY         99-7006224         South K				·			5,916,378 06/29/99	
MSS FORMATION OF ALL OXIDE SURFACE 09/26/00.  LAYERS/Bailey, Brady MSS FORMATION OF ALL OXIDE SURFACE 09/26/00.  AJT METHOD OF CONTAMINATION REDUCTION BY 03/106/98  LAYERS/Bailey, Brady.  AJT METHOD OF CONTAMINATION REDUCTION BY 99-7008224	63665         HK         AJT         METHOD OF CONTAMINATION REDUCTION BY         00106069.3         Abendoned         Hong K           53665         JP         AJT         METHOD OF CONTAMINATION REDUCTION BY         10-539667         Japan           53665         JP         AJT         METHOD OF CONTAMINATION REDUCTION BY         10-539667         Japan           3665         JR         AJT         METHOD OF CONTAMINATION REDUCTION BY         99-7008224         South K						8804123.5 3/06/98		China
AJT METHOD OF CONTAMINATION REDUCTION BY 10-539667 MSS FORMATION OF ALL OXIDE SURFACE 03/106/98 LAYERS/Bailey, Brady. AJT METHOD OF CONTAMINATION REDUCTION BY 99-7008224	35665   JP   AJT   METHOD OF CONTAMINATION REDUCTION BY   10-539667   Japan   Japan   10-539667   Japan   Japan   10-539667   Japan    ଷ		·	,	_		Abendoned	Hong Kong	
AT METHOD OF CONTAMINATION REDUCTION BY 99-7008224	3665 KR AJT METHOD OR CONTAMINATION REDUCTION BY 99-7008224 South K  4SS (463035-828)  10	83			1		0-539667 3/106/98		Japan
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Reference No.		.	- 1999			•
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		NESS	FORMATION OF ALL OXIDE SURFACE	170 Date 03/06/98	Isrne Date	Countries
63665	DS .	AJT	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE	9904262.4	67703	Singapore
63665	<b>₩</b>	ASS	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDS SURFACE	87102978 02 mm me	147013	Taiwan
<del></del>	台	AJT	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE	98910258.7 GMC408	04/15/02	Burge
	FC	AJT	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDS SURFACE	PCT/US98/04570 03/06/98	Closed	PCT
		ATT MSS	FLANGE CLAMP/Matros, Kamian	08/746,608	Abendana	
1_	2	A57 MSS	FLANGE CLAMP/Mateos, Kamisn	11/13/96 PCT/(1897/2014		
1.		<b>15</b> B			Deposition	PCT
	:	AST MEX MEX	DIRECT DRIVE ROTATIONAL MOTOR WITH AXIAL VACUUM/Monthigh	08796,300	5,921,560	
ı		AJT. MGS	INIBCTION SEAL/Miller, Veeck		07/13/99	
		15 E	EXHAUST VENT ASSEMBLY FOR CHEMICAL	08/838 887	Caused	
		ASI.			08/17/99	
			MONOBLOK INJECTION MODIFICATION Mothragh		nominationed.	
ľ	7.77	F SSM	NTRIC OXIDE COMPOUND CONDENSER/Granados			
	H	A5T	NITROGEN DILUENT GAS FREE OPER ATTON OF		59471-3 and closed	
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ı		`	ELIONIDA TITETTI	Serial No.	Patent No./	Foreign	Γ
·		MSS	FLAT PLATE DISCHARGE CELL OZONE GENERATORS/Grandos	and Survey	Lettee Date	Countries	
64873	3	12	WAPER CARRIER AND SPACONETICES				
		SQN .	APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATEATOR D. D. D.	09/018,021 02/02/98	00/2Z/Z0 685'9Z0'9		T
64873	3 1	AT	WAFER CARRIER AND SPACCOMMISSION				
	<b>,</b>	MESS	APPARATUS FOR PROCESSING A	09/457,929			Т
	•	•	SEMICONDUCTOR SUBSTRATB/Yao, Bailey	Div. of 09/018,021			
64873	2	ATT	WARR CARRES	02/02/98			
		MBS	WATER CARLIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A	2319636	Abendoned	Canada	
64873	2	H.V	SEMMICONDUCTOR SUBSTRATE/Yea, Bailey				
		MSS	WAFRK CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A	99802634.4		China	Ţ
64873			SEMICONDUCTOR SUBSTRATE/Yao, Bailey	66/10/70			
7 <b>9</b>	<u> </u>	MSS	WAFER CARRIER AND SEMICONDUCTOR AFPARATUS FOR PROCESSING A	01104936.8	Abandoned	Hone Kone	-
24043			SEMICONDUCTOR SUBSTRATE/Yao; Bailey	07/16/01	•	9	—
? }		MSS	WAFER CARRIER AND SEMICONDUCTOR APPARATING NOR DESCRIPTION	137533	Abandoned	. Israel	<del>- i</del>
	_		SEMICONDUCTOR SUBSTRATE/Yao. Bailey	02/01/99			
<b>648</b> 73	라	ASS MSS	WAPER CARRIER AND SEMICONDUCTOR APPARATIS FOR PROGRESSION	2000-529567		Tomon	· -
			SENGICONDUCTOR SUBSTRATE/Yao, Bailey	02/01/99			
048/3	<u> </u>	ATT. MSS	WAFER CARRIER AND SEMICONDUCTOR APPARATIN FIND PROCESSION	2000-7008430	376643	7.4.00	
			SEMICONDUCTOR SUBSTRATE/Yao, Bailey	02/01/99	03/06/03	Sound Profess	
04873	9	44 ×	WAFER CARRIER AND SEMICONDUCTOR	200004218-2	74007		
-			NG A		08/30/02	Singapore	
4873 573	¥.	AJT.	WAFER CARRIER/Yao, Bailey	88100710			
25	8			01/18/99	03/16/01	Taiwan	<u> </u>
2		NSS S	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR	99905586.6		Europe	
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Foreign	Countries	Z:			EG .	Canada	Chins	Hong King	Burope	Ismel	Japan	South Korres	Singanoan	Taiwan			Canada
Pertent No./	Isrue Date		5,849,088 12/15/98	6,056,824 05/02/00	Closed			Abandoned		Abandoned	3416114	04/04/03 346767	74790	08/30/02 135711	10/27/01	03/05/02	Abendoned
Serfal No./	PCT/US99/02100	02/01/99	09/008,024 01/16/98	09/185,180 11/03/98	CIP of 09/008,024 PCT/US98/25740	2318147	98813641.4	01104322.0 06/21/01.	98960728.8	137315.	2000-540285	7859	1.22	:	11/26/98	85,180	2304548
Title/Inventors	WAFER CARRIER/Yao, Bailoy	FREE PLOATING SUITE P.P. P.	Te 19 (Agrino) De Domingo, et al.	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM BETTAINED.	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bertholomers 4.01	FREE FLOATING SHIELD AND SEKICONDUCTOR PROCESSING SYSTEM RETHINGS AND SECONDUCTOR	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Christopher A. Peabody, Jay B. Dedonmey, Learning D. Benthol.	FREE FLOATING SHIELD, AND SEMICONDUCTOR PROCESSING SYSTEM Republicant	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM PARTICION AND SEMICONDUCTOR	FREE FLOATING SHIRLD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew. et al.	FREE FLOATING SHIELD AND SEMICONDUCTOR	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEMAR - 1.2.	DUCTOR	DUCTOR	I NOCESSING STSTEM/Burtholomew, et al.	PROCESSING SYSTEM/Batholomew, et al.
·	AT.	2	MSS	AJT	A57 MGSS	ASS	ASS MSS	AJT. MBS	A5T. MSS	ATT MSS	ASS MSS	ATT. MGS	AJT. MSS	-		• ]	MBS
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Reference No.	64873	65583		28559	65583	<b>EXS</b> 233	68583	65583.	65583	65583	£8559	68583	65583	65583	65583	65583	_
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Reference No.			Title/Inventore				
- 5			Limborn	Serfal No.	Patent No./	Foreign	1
65583 2-CN AJT MSS		ľ	PROCESSING SYSTEMS AND SEMICONDUCTOR.	00106454.1	Isme Date	Countries	Т
65583 2-EP AJT MSS	A5T MSS	İ	FREB FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEMS	00302953.5			
65583 2-HK AJT MSS	ATT	1	FREE FLOATING SHIELD AND SEMICONDUCTOR	04/07/00	Abandoned	adamer	
65583 2-JP AJT MSS	ASS MSS		FREE FLOATING SHIRLD AND SEMICONDUCTOR PROCESSING SYSTEM OF ALL	2000-108638		Tomag Kong	. 1
65583 2-KR AJT MSS	A-T-		FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEMES.	2000-0018645	338891	A there	
65583 2-MY AJT MSS	58		FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEMAS	04/10/00 PIZ0001457	05/20/02	Molecui.	
65583 2-SG AJT MSS	<b>4</b> 88 4	l		04/07/00 200001878.8	.	O'investigate	
65583 2-TW AJT MSS	₹ §	'		03/31/00 89106510		T. T.	
65583 2-TH AJT. MES	MSS.		FREE FLOATING SHIELD AND SEMICONDUCTOR	04/08/00 056644	Abendoned	T. T. T	
65816 AJT. MSS	<b>F</b> 888	l		04/03/00 Hold.			· · · · · ·
65965 AJT. MSS	1			09/067,704 04/28/98	6,068,884		
65965 CA AJT. MSS	ALT. MSS			2,330,040 04/15/99	Abendoned	Canada	
65965 CN AJT. MSS	ALT		LOW K DIRLECTRIC INORGANIC/ORGANIC  HYBRID FILMS AND METHOD OF MAKING/Rose;  Lopets; Felts	99806506.4 04/15/99		China	
Ħ.	AJT. MSS		LOW K DIELECTRIC INORGANIC/ORGANIC  HYBRID FILMS AND METHOD OF MAKINGROSE;	01108034.0 11/15/01	Abandoned	Hong Kong	
65965 IL AJT MSS	58		LOW K DIELECTRIC INORGANIC/ORGANIC	139128	Abrodoned		
		Ħ	FILMS AND METHOD OF MAKINGROSS; O	04/15/99		Errei	

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	Countries	Japan	South Korea	Singapore	Taiwan	Вигоро	PCT				Taiwan	PCT
Patent No.	Isrue Date			76753 12/07/02	161126 06/19/02		Closed			Abandoned	147614 0472702	Abandoned
Serfal No./		2000-545704 04/15/99	2000-7012019 04/15/99	200005999-8 04/15/99	88106881 04/28/99	99917529.2· 04/15/99	PCT/US99/08246 04/15/99	09/361,667 07/27/99	10/637,913 08/08/03	09/113,730 07/10/98	8811 <b>0478</b> 06/22/99	PCT/US99/08702 04/21/99
Title/Inventors	Constr. Bake	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lorda: Felts	LOW K DIRT BCTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopath: Fells	LOW K DIRLECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopath: Felta	LOW, K. DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopets, Felts	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopsin: Pelis	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKINGROSE; Lopset:Felis	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopsin: Felia	LOW. K. DIEL ECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felis	CHEMICAL VAPOR DEPOSITION APPARATUS EMPLOYING LINEAR INJECTORS FOR DELIVERING GASEOUS CHEMICALS AND METHOD/Doblin; Stiffer-McCiness	CHEMICAL VAPOR DEPOSITION APPARATUS EMPLOYING LINEAR INTECTORS FOR DELIVERING GASEOUS CHEMICALS AND METROD/Dobbin: Steffer-Mediment	
		ASS	AJT MGSS	AJT	AJT. MSS	AJT. MSS	AJT	AJT	AJT. MSS	AJT. MESS	AJT MSS	AJT. MSS
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Title/Inventors	DELIVERING GASTOTIS CTITIS CTITIS	METHOD/Doblém: Striffer, McGrogan	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bertholomew: Beiley: Real 4: Poles.	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METERON	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METERS	WAFER PROCESSING REACTOR HAVING A GAS FLOW, CONTROL SYSTEM AND METHOD/ Bertholomer, Relieve Perell, P. 1.		WAFER PROCESSING REACTOR HAVING A GAS FLOW. CONTROL SYSTEM AND METHOD/ Bertholomow, Beiley, Bwald; Boland
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			MSS	FLOW CONTROL SYSTEM AND METHOD/ Bertholoment: Relieve Hamelt: Dec. 1	•	Closed		T
a,	67178	∞	₹.	GAS DELIVERY METERING TIBERS AND STATES				·
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			MSS	CAS DELIVERY METERING TUBE/Ingle; Stoddard; Yao; Hamibon; Young: DeSa	09/470,446			_
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¥_	67178	MY.	AJT MGS	GAS DELIVERY METERING TUBE/Ingle; Stoddard;	05/19/00 PI-20002163			т
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A,	67178	-	ł	VERY METERING	04/07/00 Unfiled	01/09/02	TRAMBU	
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	Serial No./			07/12/02	200204131-7	07/09/02 91115232	07/09/02	07/15/02 07/370,331	06/22/89	165499/90 06/22/90		1990-9287 0672290	70106124	06/22/90	90111648.3 06/20/90	90111648.3	06/20/90		·	90111648.3 06/20/90	07/661,837 02/27/91
	Title/Inventors	GAS DELIVERY METERING TUBE/Anthony Dess; Jay	GAS DELIVERY METERING TUBE/Anthony Desa; Jay B. Dedompor Samuel Y.	GAS DELIVERY METERING TUBE/Anthony Desa; Jay B. Dedombey, Samuel F.	GAS DELIVERY METERING TUBE/Authorry Desa; Jay 20	GAS DELIVERY METERING TUBE/Anthony Dess; Jay B. Dedonthur, Surmel V.	GAS DELIVERY METERING TUBE/Dest; DeDominoy;	METHOD FOR DEPOSITING SILICON DIOXIDE	METHOD FOR DEPOSITING SIT ICON DICKTOR	FILM AND PRODUCT/Mahawili	METHOD FOR DREOSTEING SET 1001	FILM AND PRODUCT/Mahawili	METHOD FOR DEPOSITING SILICON DIOXIDE	FILM AND PRODUCT/Mahawiii METHOD FOR DEPOSITING OF FOOR PROSE	FILM AND PRODUCT/Mahawiii	MESTHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODICTIMAL SAME	METHOD FOR DEPOSITING STATION DIOXIDE	METHOD FOR DEPOSITING SILICON DIOXIDE			
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Serfal No./	Fuling Date	07/28/89	201089/90	11454/1990	79105355	90114325.5			242305/90 09/12/90	14732/90	<u> </u>	07/29/90 90115336.1			90115336.1	, , -,	08/10/90 90115336.1		03/29/91	07/668,858
Title/Inventors	CHEMICAL VAPOR DEPOSITION REACTOR AND	METHOD OF OPERATION Mahawili	METHOD OF OPERATION MANAGEMII	CHEMICAL VAPOR DEPOSITION REACTOR AND METHOD OF OPER ATTOMACA.	CHEMICAL VAPOR DEPOSITION REACTOR AND	CHEMICAL VAPOR DEPOSITION REACTOR AND	MULTI-ZONE PLANAR HRATER ASSEMBLY AND	MULTI-ZONB FLANAR HRATER ASSENDED VANDE	METHOD OF OPERATION/Mahawili	METHOD OF OPERATION/Mahawiii	MULTI-ZONB FLANAR HEATER ASSEMBLY AND METHOD OF OPERATIONALS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND	MULTI-ZONB FLANAR HRATER ASSEMBLY AND	METHOD OF OFFIRATION Mahawiii MUT. T. ZONR PI ANAP TERATER ASSESSION	METHOD OF OPERATION Mahawiii	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPER ATTOMACA.	MULTI-ZONE PLANAR HEATER ASSEMBLY AND	METHOD OF SOLDERING IN A	CONTROLLED-CONVECTION SURFACE-MOUNT REFLOW FURNACE/Alley, Camassed Dalmy Boffer.	AND TRANSPARENT FILMS OF TIN AND
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67392	완	15	METHOD FOR PRODUCING HIGHT V CONTRICED	_		
	· ·		AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIOM OXIDE BY APCYDAGOVE	33519/92 03/12/92	Abandoned	Jepan
67392	X.	A.	METHOD FOR PRODUCING HIGHLY CONNICERTE	70401		
		•	AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIUM OXIDE BY APCYDAMINE.	4458/1992 03/12/92	Abendonod	South Korea
67392	EB		METHOD, FOR PRODUCING HIGHLY CONDITCHINE	, 0000000		
	·		AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIVIN OXIDE BY APCYDIMANT.	02/27/92	Abandoned	Вигоре
67392	-	5	METHOD AND APPARATIC TOTAL			
•			HIGHLY CONDUCTIVE AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIUM OXIDE BY APCVDAMENT	07/856,457 03/24/92	Abandoned	
885/9		AT.	PROTECTIVE GAS SHIELD APPARATUS/Studdent	2003600		<del>-</del>
67588		-	PROTECTIVE SASSET	05/21/99	Closed	
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67588 	<u> </u>	AJT. MSS	PROTECTIVE GAS SHIELD APPARATUS/Stoddard;	09807884 X	06/10/03	
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		MISS	PROTECTIVE GAS SHIELD APPARATUS/Stoddard: O	00936074.4		
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	67735		AJT MSS	APCYD TEOS; OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curis; Rao; Kankin	60/127,520 04/02/99	Closed		- 1
	67735		AJT MSS	IMPROVED TRENCH ISOLATION PROCESS USING APCVD TEOS.OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curis; Reg; Kapin	09/541,395 03/31/00	6,387,764 Issued: 05/14/02		1
	67735		AJT. MISS	TRENCH ISOLATION PROCESS USING APCYD TEOS:OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH! Cartie, Res; Kapkin	23 <b>64975</b> 03/31/00	Abandoned	Canada	
<del>-,</del>	67735	ž	AJT MSS	TRENCH ISOLATION PROCESS USING APCYD TEOS: OZONE TO DEPOSIT. A TRENCH FILL OXUDE PRIOR TO SUDEWALL LINER OXIDATION GROWTH! Carti; Rao; Kaptin	00807742.8 03/31/00		China	ł
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Reference No.				•	· . •	· . •	
			Title/Inventors	Serial No./	Patent No./	Foreson	- 1
MΙ		57	TRENCH ISOLATION PROCESS LISING APPLIE	Filling Date	Lectre Date	Countries	
	<b>2</b>		TEOS:OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTE/ Cardic Res: Kinchin	04/01/00		Taiwan	
邑	·	AJT MSS	TRENCH ISOLATION PROCESS USING APCVD 1BOS.OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH CALL	00919996.9			
	PC AJT MSS	·	TRENCH ISOLATION PROCESS USING APCVD. TEOS.OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Cont. P. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1.	PCT/US00/08650 03/31/00		PCT	
	ATA WES VED	1	NEAR-ATMOSPHERIC CVD SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS/ Carvalbeins; Mayer; Menagh; Savage; Vanghan	60/127,532 04/02/99	Closed		
	AAT MESS VEU		SEMICONDUCTOR WAFER PROCESS SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheirs; Traini: Committee Venetal Statements	09/483,945 01/13/00	6,610,150 08/2,6/03		
	CA AJT MBS	i	SEMICONDUCTOR WAGER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menigh; Carvatheir; Proinni; Committee: Vanophen: Man	2369042	Abandoned	Cenada	
	CN AST MBS	l l	SEMICONDUCTOR WAFER PROCESSING SYSTEM OF WITH VERTICALLY-STACKED PROCESS. CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Sevage; Menagh; Carvalheira; Troinni; Concentine; Venghan; Mayer	008006652.3		China	
	ASS MSS		MATH VERTICALLY-STACKED PROCESSING SYSTEM  HAMBERS AND SINGLE-AXIS DUAL-WAFER  RANSFER SYSTEM/Savage; Menagh; Carvalheirs; relent; Committee Vanobare, Menagh; Carvalheirs;	15678 121/00	Abandoned	[grae]	
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₹	67736	<u>e</u>	A.	SEMICONDUCTOR WAFER PROCESSING SYSTEM	Pumg Date	Issue Date	Countries	
				WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvelhoin;	03/21/00		Japan	
FA	67736	X.	A5T	SEMICONDUCTOR WAPER PROCESSING SYSTEMS				
		• .	•	WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheim;	2001-7012462 03/21/00		South Korrea	
FA	67736	8	154	SEMICONDICTOR WATER DESCRICE	•			
ł		•		WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troisni; Committee Verreles:	200105951-8 .03/21/00		Singapore	
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AJT   SINGLE-AXIS DIJAL-WAFER TRANSFER   60/127,650   Marged into P-67736   VED		:		TRANSFIER SYSTEM/Savage; Menagh; Carvalheira; Troismi; Cossemine; Vaughan; Maver	11/27/01		
17	0/13/	•	AJT MESS VEU	SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Trainni; Cossentine	60/127,650	Marged into P-67736	
WEN   Michael; Kas    68017		AJT	IMPROVED SURFACE COMPOSITION AND METHOD FOR METAL COMPONENTS Reflection	60/130,783	Closed		
WEN   WEN	68017	1	WEN	Michael; Kane	04/23/99		
CA   MISS   CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; 2271353   Abandoned			MEN	Michael, Kana	09/480,730	6,206,973 03/27/01	
CN   MSS			NESS VELA	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;	2371343		
WEN         Michael, Kane         CHRMICAL VAPOR DEPOSITION SYSTEM/Bailey;         00808554.4           7 II.         MSS         CHRMICAL VAPOR DEPOSITION SYSTEM/Bailey;         146135         Abandoned           7 IV.         MSS         CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;         2000-613851         Abandoned           7 KR         MSS         CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;         2001-7013598         30703/00           7 SG         MSS         CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;         20010-613-5         303/03/00           7 IV         AJT         CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;         89104518         B9104518           8 MSS         Michael; Kane         03/03/00         G13/03/00         B13/03/00           9 PC         AJT         CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;         09912173.2         B           9 PC         AJT         CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;         09704644         6.485.782           1 AJT         CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;         09704644         6.485.782	_		KSS	CHEMICAL VAPOR DEPOSITION OFFICE	03/03/00	Dellommary	Camada
WEN   Michael; Kans   CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;   146135   Abandomed			ASS ASS	Michael: Kare	00808554.4 03/03/00		China
WEN   Michael; Kane   CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;   2000-613851   2000-613851   2000-613851   2000-613851   2000-613851   2000-613851   2000-613851   2000-613851   2000-613851   2000-613851   2000-613851   2001-7013598   2001-70135				Michael: Kina	146135	Abandoned	Igniel
KR   MSS   CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;   2001-7013598   1303/00   1303/				CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;	2000-613851		
SG   MSS   CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;   20010613-5   17W   AJT   CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;   20010613-5   13/03/00   13/03/				CHEMICAL VAPOR DEPOSITION SYSTEMBailey.	03/03/00		Japan
TW   AJT   CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;   89104518   03/03/00				CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;	03/03/00		South Korea
WEN	68017 T				03/03/00 · · · 89104518		Singapore
PC AJT CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; PCT/US00/05630 Closed WEN Michael; Kene 03/03/00  1 AJT CHEMICAL VAPOR DEPOSITION SYSTEM AND 09/704,644 6 485 782					03/13/00		
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	68017 1	<b>K E</b>			09/704,644	6.485.783	

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<	68048		MSS	GAS DISTRIBUTION SYSTEM BATHALO	On Tayon			T
Δ,	68073	3	A-T	CHRATICAT WANDER	10219,924 08/14/02	Abandoned		$\neg$
•		<del></del>	MSS	DIOXIDE BY USING ALKYLSILOXANE OLIGOMERS WITH OZONE FOR SUB 0.18 MICRON	60/143,198 07/09/99	Closed		
4	68073	m	A-T MSS	CHEMICAL VAPOR DEPOSITION OF SILICON	. 213 673/00			
				OLIGOMERS WITH OZONE FOR SUB 0.18 MICRON DEVICE APPLICATIONS IN THE STATE	04/04/00	10/15/02		T
₹	68073	ਤ -	AJT	CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYSILOXANE OF TON				
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			•	OXIDE FILMS USING ALKYSILOXANE OLIGOMERS WITH OZONEJain: Yng.	2001-509075 06/15/00		Japan	<u> </u>
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¥	68073	8		WITH OZONEJain; Yuan	06/15/00	٠.	South Kares	
			MSS	OXIDE FILMS USING ALKYSILOXANE OLIGOMERS	06/15/00		Singapore	
¥.	68073	Δ <u>I</u>	AJT MSS	CHEMICAL VAPOR DEPOSITION OF SHICON OXIDE FILMS USING ALCYLSHOXANE OLIGOMERS WITH OZONE	8911343 <i>5</i> 07/06/00	153183 07/25/02	Taiwan	
毘	68073	嵒	AJT. MSS	ON OF SELICON LOXANE OLIGOMERS	00939940.3 06/15/00		Europe	
단	68073	23	AJT. MSS	OSITION OF SILICON CYLSILOXANE	PCT/US00/16642	Closed	PCT	
A.	68244	$\prod$	AT.		2007			
-					60/143_285	7		

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		<b>.</b> .		Title/Inventors	Serfal No./	Patent No./	Foreign	
		·	MGS	DIOXIDE DEPOSITION CHAMBERS USING COMBINATION FLUORINE CHEMISTRIBS/Mayer, et al.	17/12/99	Isrue Date	Countries	.
<b>V</b>	68244	4	AJT MGS	METHOD FOR IN-SITU CLEANING OF SILICON DIOXIDE DEPOSITION CHAMBERS USING COMBINATION FLUORINE CHEMISTRIES/Mayor, et al.	09/615,035 07/12/00	6,544,345		
FA	68244		AJT MSS	METHOD AND SYSTEM FOR IN-SITU CLEANING OF SEMICONDUCTOR MANUFACTURING EQUIPMENT USING COMBINATION CHEMISTRIESMAyer, etal.	00811232.0 07/12/00		China	1 '
FA	<b>68244</b>		AJT MSS		2001-509320 07/12/00		Japan	1
FA	68244	<b>x</b>	AJT. MESS		2002-7000480 07/12/00		South Korea	- 1
FA	68244	<b>B</b> .	AJT. MSS		200200181-6 07/12/00		Singapore	
FA	68244	T.	AJT MSS		89113887 07/18/00		Taiwan	••
FB	68244	邑	AJT. MESS TJH		00958006.9 07/12/00		Burope	
£:	68244	2. 2.	AT		PCT/US00/40359 07/12/00	Closed	FCT.	1
I I	88628		<b>15</b>		60/166,662	Closed		
1059128	MISS (46)	F/1935/MSS (463035-828) 1059128	:	27			10.69.01	2

	Reference No.	1						
		· •		Title/Inventors	Sertal No./	Patent No./	Borne	ſ
			· SSSW	INORGANIC/ORGANIC DIEL ECTRIC FILMS/Lopata;	Filing Date 11/19/99	Large Date	Countries	
4	. 68628	8	AJT. MSS	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopate; Felts	09/715,455 11/17/00			
FA	8628		AJT MSS	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopan; Felts	00816928.4		China	
FA .	82289	स स	AJT MSS	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	2001-538578		Japan	
¥.	68628	X)	AJT: MSS	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Fells	11/17/00		South Kores	
FA ·	8238	MY	AJT MSS	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopate; Felia	PIZ0005431. 11/20/00		Malaysia	7
FA	8228	80	ATT	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopate; Felds	11/17/00		Singapore	
FA	68628	ΨL	A-T- MSS	SYSTEM AND METHOD FOR DEPOSITING INORGANICORGANIC DIED PORTED	89124488	·	Ė	
E	68628	且	AJT.	SYSTEM AND METHOD FOR DEPOSITING INORGANICORGANIC DIELECTRIC FILMS/Lopatz; Pelis	11/18/00 00980511.0 11/17/00		Latwan Burope	<del></del>
랊	8628	2	AJT. MSS	THE AND METHOD FOR DEPOSITING GANICORGANIC DIFFERENCE FILMS/Lopata;	PCT/US00/31694 11/17/00	Closed	PCT	<del></del>
	68894		A-TT MSS.		06/412.237	4 646 3000		
FA:	68894	NV.		ION APPARATUS AND		10/08/85		·
<u> </u>	68894	<u>ર</u>	ASS	<del>-   `</del>		Abendoned	Australia	
1 .		4	7	ACCESSOCATION Miller		1,196,777. 11/19/85	Canada	

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• •	Patent No.	Into Date	Abendoned	Apendoned	80079	Abundoned	1446905	Abendoned		10/484	4,539,933	09/10/85	572883 08/30/84	1,216,419	Abendoned	1,236,970 05/24/88	Abendoned	23307 12/28/85	Abandoned	0137702	Abandoned	4,548,159	1451172	07/25/88
٠	Serial No.	State Sums	60170	07/06/83	80079	_	155171/83 08/26/83		000000000000000000000000000000000000000	10/02/84	06/528,193	08/31/83	08/30/84	462,110 08/30/84		515,262 08/01/86		73103596 08/30/84		84305932.0 08/30/84		07/06/84	146857/85	07/05/85
- 1774	This/Inventors		CHEMICAL VAPOR DEPOSITIONS PROCESS/	CHRAICAT VAROR PROCESS	Cumpbell; Miller	CHEMICAL VAPOR DEPOSITION AMAGE AMAGES	PROCESS/Campbell; Miller	CHEMICAL VAPOR DEPOSITION APPARATUS AND PROCESS/Cempbell: Miller	CHEMICAL VAPOR DEPOSITION APPARATITIS AND	PROCESS/Campbell; Miller	CHEMICAL VAPOR DEPOSITION APPARATUS/	CHEMICAL VAPOR DEPOSITION APPARATITIS/	Cumbbell; DuBois; Manriquez; Miller	CHEMICAL VAPOR DEPOSITION APPARATUS/ Campbell; DuBois; Mamiquez; Miller	CHEMICAL VABOR DEBOGIETON .	Campbell; DuBois; Maniquez; Miller	CHEMICAL VAPOR DEPOSITION AREAS	Campbell; DuBois; Mauriquez; Millor	CHENGICAL VAPOR DEPOSITION AMARA		APOR DEPOSITION WARRE BOAT	Foster, Herring	CHEMICAL VAPOR DEPOSITION WAFER BOAT/	
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Reference No.	او	]  -				•	
	·		Title/Inventors	Serial No./	Patent No.		,
16889	6	¥.	CHEMICAL VAPOR DEPOSITION WATER BOAT	Filing Date	Issue Date	Countries	
68897	4 <u>2</u>	ALT	CHEMICAL VANDS DEBOGETIES: WALTEN BOAL!	05/04/84	4,582,020 04/15/86		
	·	MBS	Loam; DuBois	480,118 04/25/85	1,234,972	Canada	
<b>26889</b>	ei Fi	ASS	CHEMICAL VAPOR DEPOSITION WAFER BOAT/	93957/85	Abendoned		
68897	-	<b>15</b>	CHEMICAL VAPOR DEPOSITION WATER BOATE	05/02/85	04/22/91	Jepan	
		WSS	Loam; DuBois	06/804,954 12/05/85	4,641,604 02/10/87		
76889	77	15	CHRAICAT WARDS BEING	Continuation of 06/607,065	Abandoned		
: .		MSS	Learn; DuBois	06/828,625 02/10/86	4,694,778		
·				Continuation of	Abandoned		
88898		<b>FA</b>	PRIMARY FLOW CVD APPARATTIS COMPRISING	00/007,065			
			SUBSTANTIALLY EDDY-FREE GAS FLOW/Logm;	04/25/91	5,320,680 06/14/94		
86889	8	AT	PRIMARY FLOW CVD APPADA TETER ASSESSED				
			Loun; DuBois; Miller, Sollheimer	2,109,198 04/09/92	2109198	Camada	
86889	e:	AJT MES	PRIMARY FLOW CVD APPARATUS AND METHOD/	510862/92	Abendoned		
86889	Ħ		PRIMARY FLOW. CVD APPARATUS AND METHOD/	.	05/25/01	rapan	
86889	B		_		07/05/00	South Korea	
		٠,	-	92911855.2 04/09/92	0585343 12/08/99	Switzerland	
868899	DB	AJT.		92911844.9	Abendoned		
88898	El El	-	PRIMARY FLOW. CVD APPARATUS AND METHOD!		1.0	Germany	
868899	E.	T			12/08/99	Europe	
		1		92911855.2	0585343		

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				Thie Inventors	Seriel No./	,	
L	L	$\mid$	Mee		Filling Date	Transfer No.	Foreign
臣	90009	_	or i	Lorm; DuBois; Miller, Seilheimer	04/00/00	ALLEGATE L'ALLE	Countries
3	8	<u> </u>	<u> </u>	PRIMARY FLOW CVD APPARATUS AND METHOD,	04/09/92	12/08/99	
巴	86889	# E	1 <del>7</del>	PRIMARY H CW CATT A THE ATTENDED	04/09/92	0585343 12/08/99	United Kingdom
-	-		MSS	Loun; DuBois; Miller; Sailheimer	92911855.2	0585343	Table
ਜੂ ਜ	86888 	Z ®	AT. MSS	PRIMARY FLOW CVD APPARATUS AND METHOD/	04/09/92	12/08/99	(mar)
뫒	86889	S PC	45.	PRIMARY FLOW CVD APPARATUS AND MRTHODY	04/09/92	12/08/99	Netherlands
⋖	88		<b>A5T</b>	THERMAL PROCESSING APPLACEMENT	04/09/92 04/09/92	Closed	PCT
		_	MSS	PROCESS/Porter, Sanchez, Kowalski	08/399,108	5,626,680	
∢ .	66889	<u>-i</u>	AT.	THERMAL PROCESSING APPARATUS AND	03/03/95	05/06/97	
				I M. Lass / Parter; Sanchez; Kowalski	11/28/95	5,679,168	
£	66889	1-PC	<b>4</b>	THE AND	CIP of 08/399,108		
毘	8889	<u> </u>	SS E	•	PCT/US96/02440 · 03/04/06	Closed	PCT
			MSS.	TUS AND	96906598.6		
FA	66889	47	ATT		03/04/96:	·	Europe
Z.	66889	T. XX	47		09/10/60 09/10/97		Japan
	9	_ •	MSS		706100/1997		South From
:	6	٧٠	MSS	THERMAL PROCESSING APPARATUS AND PROCESSIX oble, Jr.; Dip; Engdahl; Oliver; Ratliff	08/563,875	5,618,351	
82	68839	2-PC	4		00	04/08/97	
毘	8883	5			PCI/US96/18731	Closed.	PCT
					9.8	0864170	
F.A.	68889	2-JP	A-T MSS	THERMAL PROCESSING APPARATUS AND PROCESSIVAL TO STATE OF THE STATE OF	11/22/96		edoma
FA	66889	2-KR	5		11/22/96		Japan
1				PROCESS/Koble, Ir.; Dip; Engdahl; Oliver, Radiff	703960/1998 11/22/96		South Korea

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ä	Reference No.						
		S	•	Title/Inventors	Serial No./	Patent M.	3
FA	66889	2-TW	AT	THERMAL PROCESSING APPLANT	Filing Date	Icrue Date	Foreign Countries
	.		MISS	PROCESS/Koble, Jr.: Dip; Engdahl: Oliver Rediff	86101168	NI-094773	Taiwan
. ₹	2000		14 × ×	METHOD OF LOADING AND UNLOADING A	06/719 400	06/11/98	•
V	90689	=	A5T	SEMICONDUCTOR WATER BOART C.	04/03/85	01/13/87	
	•		MSS	RELEASABLE MOUNTING/Aldridge; Elloway; Fritz; Goff, Herres	06/380,460 06/30/86 Div. of 06/719,409	4,721,424 01/26/88	
K	00689	2	AT	SEMICONDICTION WATER PRINCE		Reinstateod	
			. SSW	Aldridge; Elloway; Fritz; Goff, Herrera	06/880,422 06/30/86	4,692,115 09/08/87	-
¥	00689	3	AJT	SEMICONDUCTOR WAPER BOATTOARD	Div. of 06/719,409	Abandoned	
			WESS	CONTROL SYSTEM	06/880,423 06/30/86	4,684,863	
	68901		AST	GAS SCAVENGER / Predo:	Div. of 06/719,409	Abandoned	
		,	MSS.		06/919,736 10/16/86	4,711,197 12/08/87	
FA ·	10689	ঠ	ATE	GAS SCAVENGER/Tsving		Abandoned	•
			MSS		345,025 08/21/87	1,277,442 12,04,90	Camada
FA	10689	ei Ei	AT	GAS SCAVENGER/Tsylor		Abendoned	
T	68902	<u> </u>		WAI: PROCESSING APPARAMENT		2642936 05/02/97	Japan
	$\neg$				42	6,005,225.	
F.A.	08302	<u> </u>	A-T: MSS	APPARATUS/Kowalski;	10787/1998	12/21/99	
FA	20689	2			03/27/98		South Kares
<del>                                     </del>	68902	WT			03/25/98		Japan :
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H	68902			ONDUCTOR THRRAAL PROCESSOD WITH		•	Europe
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MSS   RECIRCULATING HEATER EXHAUST COOLING    -AU AJT   SEMICONDUCTOR THERMAL PROCESSOR    -AU AJT   SEMICONDUCTOR THERMAL PROCESSOR    -AN SEMICONDUCTOR THERMAL PROCESSOR    -BE AJT   SEMICONDUCTOR THERMAL PROCESSOR    -BE AJT   SEMICONDUCTOR THERMAL PROCESSOR    -BE AJT   SEMICONDUCTOR THERMAL PROCESSOR    -BE AJT   SEMICONDUCTOR THERMAL PROCESSOR    -BE AJT   SEMICONDUCTOR THERMAL PROCESSOR    -BE AJT   SEMICONDUCTOR THERMAL PROCESSOR    -BE AJT   SEMICONDUCTOR THERMAL PROCESSOR    -BE AJT   SEMICONDUCTOR THERMAL PROCESSOR    -BE AJT   SEMICONDUCTOR THERMAL PROCESSOR    -BE AJT   SEMICONDUCTOR THERMAL PROCESSOR    -BE AJT   SEMICONDUCTOR THERMAL PROCESSOR    -BE AJT   SEMICONDUCTOR THERMAL PROCESSOR    -BE AJT   SEMICONDUCTOR THERMAL PROCESSOR    -BE AJT   SEMICONDUCTOR THERMAL PROCESSOR    -BE AJT   DOUBLE WALL REACTION CHAMBER    -BE ASSWARRFOWING PATTER, COPAIGH; Wiesen    -BE ASSWARRFOWING PATTER, COPAIGH; Wiesen    -BE AJT   DOUBLE WALL REACTION CHAMBER    -BE ASSWARRFOWING PATTER, COPAIGH; WIESEN    -BE ASSWARRFOWING PATTER, REACTION CHAMBER    -BE ASSWARRFOWING PATTER, COPAIGH; WIESEN    -BE ASSWARRFOWING PATTER, COPAIGH; WIESEN    -BE ASSWARRFOWING PATTER, REACTION CHAMBER    -BE ASSWARRFOWING PATTER PATTER COPAIGH; WIESEN    -BE ASSWARRFOWING PATTER PATTER CO	Patent No.	Issue Date	00/60/50	.							6,101,844	746022	Abendon					A L		Closed	2000	
1-AU ATT SEE RECT AND AND AND AND AND AND AND AND AND AND	Sertal No./	Filing Date	02/10/98 CIP of 08/827.542	15511/99	2,261,391	99300910.9	00100999.1	11-072438	02/10/99 4492/1999	02/09/99	09/022,056	15512/99	2261,394	11-072437	02/10/99	4491/1999	99300909.1	02/09/99	02/18/00	60/096,283	09/3/73 894	
1-AU ATT MSS 1-TR AATT MSS 1-T	Title/Inventors	RECIRCIL ATTING HEATER STATE SALE	SYSTEM/Bolton; Wiesen	SEMICONDUCTOR THERMAL PROCESSOR RECIRCULATING HEATHR Rown. Wissen	SEMICONDUCTOR THERMAL PROCESSOR RECIRCUIT ATING HEATER DOLL THE	SEMICONDUCTOR THERMAL PROCESSOR RECIRCUL ATING HEATER POLITICAL	SEMICONDUCTOR THERMAL PROCESSOR RECIRCULATING HRATHRADOL WITH	SEMICONDUCTOR THERMAL PROCESSOR RECIPCOL ATING HEATER POST.	SEMICONDUCTOR THERMAL PROCESSOR RECTROST ATTACK	DOUBLE WAT I BEACHON CELL COM	B	DOUBLE WALL REACTION CHAMBER GLASSWARE/FOWIET PRIVIN: Krawled: Ul	DOUBLE WALL REACTION CHAMBER	DOUBLE WALL REACTION CHAMBER	OLASSWARR/Fowler, Pavin; Kowalski; Wiesen	CLASSWARE/Fowler, Parvin: Kowalaki: Wiesen	DOUBLE WALL REACTION CHAMBER GLASSWARPForder Project	DOUBLE WALL REACTION CHAMBER	LLANS WAKE FOR Parvin; Kowalski; Wiesen I MHAP PET PET COMPANY	A STATE OF THE STA	HOT WALL RAPID THERMAL PROCESSOR RAHIFF	Our Kowalski: Yadollahi: Sadahi
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	rence No	L		70690	<b>20689</b>	68902	68902	20689	68902	68903	8	5000	68903	68903	7-			1	50689		50689	

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	-		NSS.		Filling Date	Lerne Date	Countries
<	68905	5 1	15 5	HOT WALL RAPID THERMAL PROCESSOR PROCESSOR	. 00//0//00		
肚	88905	2-1-30	A P	Kowalski HOT WATT BATT BATT	09/638,113	6,462,310 10/08/02	
		_		Kowalski	PCT/US00/22202	Closed	A.L.
\$	\$300	<u> </u>	A T	HOT WALL RAPID THERMAL PROCESSOR/Radiiff	08/11/00		
		_	MBG	Kowalaci Qin	08/11/00		China
<b>≲</b>	88902	<u> </u>	A5T MSS	HOT WALL RAPID THERMAL PROCESSOR/Ratliff, Kowalski; Qiu	2001-517110		Jones
F.	50689	Ä	MBG	HOT WATT BARE	08/11/00		
			MISS	Kowalski, Qin	2002-7001786		South Korea
FA		1-MY	ATT	HOT WALL RAPID THERMAL PROCESSOR Ruliff	130005	•	·
FA	50689	1-8G	1 T	Kowalski-Qin	08/11/00		Malaysia
			MSS	Kowalski-Qin	Unfiled		Singmore
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图	50689	1	2 2		08/11/00	149415 05/17/02	Taiwan
			MSS	AND KAPID I HERMAL PROCESSOR/Radiff	00957426.0		þ
•	\$06890	7	AJT. MSS	APID THERMAL PROCESSOR/Kowalski	09/934 952	( 400 (0)	odoma
¥.	50689	m	MSS			12/10/02	
	50689	4	MSS	Ratliff	09/30/02		·
	50689	2	MSS			•	
1	90689		AZI			Unfiled	
				Bois	06/529,415. 4 09/06/83 0	4,524,719 0625,85	
$\exists$	6880		77	LOW TEMPERATURE SILICON NITRIDE CVD			•
						4.720.395	

Reference No.	S. Z.						
			11de/Inventors	Serfal No./	Patient No./	Posses	Γ
L	-	MSS	PROCESS	Filing Date	Lorue Date	Countries	
	<del>.</del>	<del></del>		08/25/86	01/19/88		Т
80689	80	5	PULSE WIDTH MONII ATER BRIDGE SECTION		Abendoned		
		MSS	SYSTEM FOR CHEMICAL VAPOR DEPOSITION APPARATUS/Johnson: Ellion	06/845,212 .03/27/86	4,728,869		T
60689	8	ATT	HOT WALL DIFFUSION FURNACE AND METHOD FOR OPERATING THE WIDNACE AND METHOD	CLF of 06/813,915 07/181,787	4,886,954		
01689	10	124	METHOD AND APPARATITE FOR DEPLOYING	04/15/88	12/12/89		
		MESS	PRODUCTS OF CHEMICAL VAPOR DEPOSITION FROM OIL FOR VACUUM PUMP/Forter	06/029_525 04/12/79	4,228,004 10/14/80		1
11689 11	<del></del>	AJT. MSS	MASS FLOW CONTROLLER/Doyle	06/193.876	4 658 855		
68912	12.	15	DIFFUSION FURNACE MILITATION FOR THE PROPERTY OF THE PROPERTY	10/03/80	04/21/87		
18		MSS	CONTROLY.	06/864,676	4,711,989		7
98913		<u> </u>	WAFER BOAT TRANSFER TOOL/Mello	09/61/60	12/08/87		
	<del></del>	SCH		05/16/86	4,728,746		
68914	4	157	WAFER TRANSFIR STAND		Abandoned		
		MSS	•	05/12/87	4,721,427 01/26/88		<del></del>
					Abandoned		<del></del>
68915	5	ATT	SENSOR FOR BATCH-TYPE		Reinstated		·
68916	. 9		NK/Radier	02/17/98	Abandoned .		г
	•	MSS VE	Nguyan BLOCK FLUID DELIVERY SYSTEM	09/388.216 09/01/99	Abandoned		
91689	MI 9	A57 MSS	LAYERED BLOCK FLUID DELIVERY SYSTEM/Newson		140378	Teimen	<del></del>
91689	2 2	AT	RED BLOCK FLUD DELIVERY		08/21/01		
ŀ		MSS	·	08/03/00	Abandoned	PCT	<b></b> -
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15		MODULAR FLUID DEI TURBY CUCIERS AND	Filing Date	lerue Date	Foreign
VE VE		Baylogue at 81 Edwinguyen	09/800,595 03/06/01 CIP of 09/388,216		
58		MODULAR FLUID DELIVERY APPARATUS Nguyen	02/106830.3	:	
28			2002-059114	·	Comma
A SS			03/05/02		Japan
<b>F</b> 88	-	MODULAR FLUID DELIVERY. APPARATUSNEDEN	03/06/02 PIZ0020747		South Kores
ASS S		MODULAR FLUID DELIVERY APPARATUSNED 2	200201201-1		Mainyara
A SS		MODULAR FLUID DELIVERY APPARATUSNguyen   9	91103478		Singapore
15 88 15 88 16 88		MODULAR FLUID DELIVERY. APPARATUS Nguyen   0	02251573.8		1 arwan
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- 1.			05/04/01 (filed by		Co-owned with Deposit
MSS	- H	Sella;		Unfiled	
MSS		MODEL BASED TEMPERATURE CONTROL OF BATCH FURNACE/Oh		Unfiled	
MESS		H	09/628,471	6,476,921	Co-owned with
MSS	I S		-	Closed	MIT, all foreign as well
17 8	HÀ		12/29/00:		
1	-	POLISHINGSsir; Lai; Oh	12/21/01		Co-owned with MIT, all foreign

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Reference No.	.			•		
•	•		Title/Inventors	Serial No.	Patental	
	69174 I-CN	MSS	IN-SITU METHOD AND APPARATUS FOR END	Filling Date	Isme Date	Foreign Countries
	69174 1-JP.	MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION	2002-516606		China Japan
69174	Ţ.	MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION	2003-7001394		, A
69174	1-MY.	ATT	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION IN CHEMICAL MECHANICAL POLISHINGAL:: 8-1-0-1-0-1-0-1-0-1-0-1-0-1-0-1-0-1-0-1-	01/31/01 F1 20013602		S. Lores Malaysia
69174	1-8G	MSS	IN-SITU METEOD AND APPARATUS FOR END POINT DETECTION	200300662-4		
69174	1-TW	MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION IN CHEMICAL MECHANICAL POLISHINGMENT SOLD OF	01/31/01 90118624 07/31/01	158247. 10/18/m2	Singapore
69174	1-PC	MSS		1/24146	Clased	PCT
69175	. ,	MSS		09/628.563 07/31/00		Co-owned with
52169	ZW.	MSS	RATUS AND METHOD FOR CHEMICAL ANICAL POLISHING OF SUBSTRATESMAIVIN:	PIZ0013601		MIT, all foreign as well Malaysia
<del> </del>	TW	MSS		90118623 97731/01		Taiwan
69175		MSS	ij		Closed	
447 kin	<b>陸</b>		Suh;	10.22.701		Co-owned with
<u> </u>	I CN	MESS	IS AND METHOD FOR CHEMICAL	01815145.0		atti, all foreign as well China
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13	Reference No.	8					
		1		Title/Inventors	Serial No./	Patent No./	Dente
FA	52169		MSS	APPARATUS AND METHOD FOR CHEMICAT	Fifting Date	Issue Date	Countries
¥	69175	T.	MSS	APPARATUS AND METHOD FOR CHEMICAL	10/15/101		Japan
FA	69175	1-80	MSS	APPARATUS AND METEOD FOR CHEMICAL	01/31/01		South Korea
FA	69175	頁	MSS	APPARATUS AND METHOD FOR CHEMICAL	01/31/01		Singapore
£;	69175.	1-PC	MSS	APARATUS AND METEOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Melvin;			Europe
4	69175	2	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Sub;	Closed		
¥	69228		MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/Lai; Saka; Oh	09/628,962 07/31/00	6,458,013	Co-owned wiff
FA	82269	Z	MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/1 of solution	01815147.7		as well
FA	82289	ej.	MSS	METHOD OF CHEMICAL MECHANICAL	07/31/01		Cema
FA	82269	Ħ.	MSS		07/31/01		· meder
FA		MY.	MSS		07/31/01 PI20013603		South Korea
e:	82269	2 2	MSS	MECHANICAL	07/31/01. PCT/US01/24170		Malaysia
	69228	8	MSS		07/31/01 2003006/51.2		Į.
. •	87769	WI	MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/1 at 80 at 50	90118625		Singapore
毘		a B	MSS	-	07/31/01		Larwan
	69229	<b>A</b>	MSS	CIN THE	13	Closed	· edama
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Refe	Reference No.				•			
				Title/inventors	Sertal No.	Patent No./	Foreign	Г
				Lai; Sala; Clam	Fifting Date	Issue Date	Countries	
⋖	825	·	MSS	CHEMICAL MECHANICAL POLISHING OF COPPER.	10067 477			T .
				OXIDE DAMASCENE STRUCTURES/Sakai; Lai; Oh			Co-owned with	T -
<u></u>	69229	ည္	MSS	CHEMICAL MECHANICAL POLISHING OF COPPER.	PCT/US02/0254		as will	
4	69274		MSS	METHOD AND APPARATUS FOR TRANSPERSENCE			Į.	
				WAFERS BETWEEN CASSETTES AND A BOAT/ Enghos: Wobber, Earlings: Nightrams: Schumen: V.	05/16/86	4,770,590 09/13/88		<del></del>
¥	69274		MSS	·	90/006,018 05/21/01	Ro-examination of Patent No. 4,770 590		
FA .	69274	DB.	MSS	METHOD AND APPARATUS FOR TRANSFERRING	P3715601.2	315707		
FA	69274	DB-1	Mgg	Hugher, Webber, Harlinger, Nishikawa; Schuman; Yee	05/09/87	07/06/00	Germany	·
				TUS FOR TRANSFERRING SSETTES AND A BOAT Nishipana Sal	P3745134.0 01/24/96	03/04/99	Germany	
FA.	69274	FR	MSS .		8706851	8706851		•
FA	69274	FR-1	MSS	APPARATUS/ Herlinger;	05/15/87	08/21/92	Prance	
FA	69274	H	MSS	$\neg$	11/19/87	08/21/92	rance .	
FA	4000			WAFERS BETWEEN CASSETTES AND A BOAT/ Higher, Webber, Herlinger, Nishikawa, Schuman, Yee	4793UA/87 05/14/87	1206283 04/14/89	Italy	
		÷ .	SCAM	<del>                                     </del>	62-1171 <i>97</i> 05/15/87	2681055 08/08/97	Jepan	
 ≰	69274	<b>8</b> 9	MSS		8711230 05/13/87	2190345	Great Britain	
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	1					08/15/90	Great Britain	•
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				Title/Inventors	Serfal No /		
¥	70769	\$	MSS	NON-CONTACT CAP MACEINE	Fifing Date	Istae Date	Foreign Countries
۵,	69447	14	MSS	SYSTEM AND METHOD TO COMPANS		CLOSED PER CLIENT	
K	69447	14	MGS	DELTA-TPOTES, Stemen SYSTEM AND METHOD TO COMMON	60/274,532 03/08/01		
8:	69447	#7 PC	MSS	DELTA TEMPERATUREI/Porter, Stamor SYSTEM AND METHOD TO CONTROL BADIAY	10/095,974 03/08/02		
FA	69447	\Z \	MSS	SYSTEM AND METHOD TO CONTROL RADIAL	PCI/US02/07034 03/08/02 02800595 3		<b>FCI</b>
FA	69447	7. JP	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DIELTA TRAFFIRM ATTEM.	2002/572612	·	China
FA	69447	TR.	MSS	SYNTEM AND METHOD TO CONTROL RADIAL	2002-7014904		Japan
FA	69447	7 MY	NCS S	SYSTEM AND METHOD TO CONTROL RADIAL	03/08/02 P120072460		South Korea
FA	69447	98.	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERA ATTENTION	200206968-0		Malaysia
FA	69447	7 TW.	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DRI TA THANKER ATERIA	03/08/02		Singapore
FB	69447	日	MSS	SYSTEM AND METHOD TO CONTROL RADIAL	06/25/02		Taiwan
	69448		MESS	INERTIAL TEMPERATURE CONTROL/Sumer			Вигоре
	69448		MSS	INERTIAL TEMPERATURE CONTROL/Statuct		. Danne	·
FA	69448	z	MSS	INERTIAL TEMPERATURE CONTROL/Stamer	02/06/02.		
FA	69448	라	MGSS .		02/06/02 2002-060336		China
$\Box$	69448	Ž.	MSS	NERTIAL TEMPERATURE CONTROL/Stamor	2007-6778		Japan
FA	69448	MY	MSS		02/06/02 02/06/02		South Kores
			-	•	02/24/02		Malayaia

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Refe	Reference No.	١.						
		2	•	Title/Inventors	Serfal No.	Parkent No.		Į.
F.	69448	8	SSEW	INERTIAL TRAPER ATTER COMMISSION	Filing Date	Isrue Date	Countries	
FA	60448	E	- 1	TOYP CONTROL State	200200733-4		Singmore	
			SS SS	INERTIAL TEMPERATURE CONTROL/Stamer	91101797	1.000	· ·	J
班	69448 8	卧	MSS	INERTIAL TEMPERATURE CONTROL/Shamer	02/01/02	07/07/03	Teiwan	
V	69477	L	MSS	NOW CONTACT CASE AND WOOK	02/06/02		Burope	1
Ы	67369		MESS	APPARATINE BOD THE INTERNAL		Closed.	-	- 1
		•		DEPOSITION OF THIS PREFERENTIAL DEPOSITION OF THOS HOS BASED SION THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayor; Ingle; Mamphy;	60335,494 11/01/01	Closed	<del> </del>	l l
¥	62869		MSS	APPARATUS FOR THE PREFERENTIAL				•
		•	AGW.	DEPOSITION OF TEOS+03 BASED SION THIN FILMS ON SILICON SURFACE RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Ingle; Mumphy; Mettern: Kirita	11/01/02			1
FA .	62869	3	MSS	APPARATUS FOR THE PRHESED FT 1.				
			MBG	DEPOSITION OF TEOS+03 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES Mayer, Ingle, Murphy, Mathon; Knita	11/01/02		Chins	ı
FA FA	62869	.E.	SSW	APPARATUS FOR THE PREFERENTIAL				
				DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Ingle, Murphy, Mathers, Emilia	201226 11/01/02		Japan	i i
₹ .	2888 8888	ğ	MSS MDV.	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOSHO3 BASED SIOX THIN	28.601	,	South Korra	- 1
				FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; ingle; Murphy; Methon; Kurin.	70/15/D3			
<u></u>	<u>4</u> 62869	MY.	MSS		PI20024020			
				FILMS ON SULICON SURFACES RELATIVE TO SULICON-NITRIDE SURFACES/Mayer; Ingle; Murphy; Mathers, Karita	10/28/02		Malayan	•
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12	Reference No.	١				·.	
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FA	62869	08	MSS	APPARATUS FOR THE PREFERENCE	Filing Date	Isrue Date	Foreign
•			N D D	DEPOSITION OF TEOSHO3 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES MANNET LATER TO	200206557-1 10/28/02		Singapore
#A	62869	A.	MSS	APPARATUS FOR THE PRESENTING.		•	•
			WBG WBG	DEPOSITION OF TBOS+03 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayor; Ingle; Murphy; Mathem: Kmit.	9112 <i>5</i> 270 10/25/02		Taiwan
毘	62369	卧	MSS	APPARATUS FOR THE PREFERENTIAL	2 0074400	:	
			MBG	FILMS ON SILICON SURFACES RELATIVE TO SELICON-NITRIDE SURFACES RELATIVE TO SELICON-NITRIDE SURFACES/Mayer; Ingle; Mauphy;	01/01/02	•	Вшоре
<u>a</u>	70028		MSS	MULTILAYER HIGH DIRITECTRIC CONSTANTS	·		
₹.	70028		MSS	OXIDE FILMS AND METHOD OF MAKING/Senzald	60264,428 01/26/01	Closed	
				FILMS/Senzaki	10/056,625		
4	70232		AT	FLUOROPOLYMER INTERLAYER DIRLECTRIC BY	70.6770		
<del></del>				Treat, Brichic, Lopata, Rose	60/288,653 05/04/01	Closed	Application is co- owned with DuPont
			\$	FLU			To be filed by
	•		Med.	CHEMICAL VAPOR DEPOSITION/Lopata; Mocella	10/137,875 May 2, 2002		Application is co-
A	70380						To be sing.
	3		NO.	HALIQUID	60/337 566	Ę	DuPont counsel
∢	70380		MSS	TH A LIOUTD	11/30/01	Cabboo	
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	2	Countries	Taiwan	12				S S		South Korea	Malaysia	i	Singapore	Taiwan		Епторе				Office
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	Serial No./	Filing Date	11/26/02	US02/38178	<del></del>	_						08/19/02 200205046-6	08/20/02	08/19/02			X S		07/12/02	02141805.5 07/15/02
	This Inventors	HIGH FLOW RATE BUBBLER SYSTEM AND	HIGH FLOW RATE BUBBLER SYSTEM AND	METHOD; Torioman	APPARATUS AND METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lones	APPARATUS & METHOD FOR INSULATING A SRAI	APPARATUS & METHOD FOR INSULATING A SHAT	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS	APPARATUS & METHOD FOR INSITE ATTACK A CELET	IN A PROCESS CHAMBER/Draper, Robinson; Lopes APPARATITS & METHOD TON	IN A PROCESS CHAMBER/Draper, Robinson: Lones	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER.	SYSTEM AND METHOD FOR DEPOSITING	INORGANICORGANIC DIELECTRIC FILMS/Draper;	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CELL IN A PR	CHEMICAL VAPOR DEPOSITION SYSTEM FOR	MODULAR INTECTOR AND EXHAUST ASSEABLY/	_		
	i	SSW	MSS		WEN	MESS WEN	MSS	MSS	MSS	MSS ·		MSS	AST.	MBG	MSS	MSS	MSS	MSS		MBG MBG
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	Patrent No.	Lerne Date					· .					This petrot appln. is	co-owned with				Closed							
	Serial No./	Filling Dete	07/15/02		2002-0040964 .	PIZ0022636	20/11/02	07/12/82	91115568	<b>2021</b>	07/15/02	Prepared and	Infineon counsel				60/310,026. 08/03/01	1001000	08/02/02	08/08/02	2000	08/05/02	2002-0044080	
	Title/Inventors	MODULAR INJECTOR/DeDontley: Metthiese: F		MODULAR INIBCTOR/DeDontley: Matthissen: F.	BITTING TOPONOMICS (C.	MODULAR INIBCTOR/DeDontley; Matthiesen; Kurin	MODULAR INIECTOR DeDontley, Matthiesen: Kmin		MODULAR INIECTOR/DeDontley, Mathiesen; Kurita	MODULAR INIECTOR/Dedouter: Mathians: Ei-	HEATING SYSTEM AND ASSESSED.	AN ATMOSPHERIC REACTION Breeden: Seidemenn:	Mostler			DEPOSITION OR I OW STREET	BORON DOPED SILICA FILMS FOR OPTICAL WAVEGINDERACE	OXIDE STRUCTURE AND METHOD OF FORMING	OXIDE STRUCTURE/Mognard	WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/ Monney	T	STRUCTURE/MORRING THE		
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	Title/Inventors	WAVEGUDE AND METHOD OF FORMER	OXIDE STRUCTURE/ Mogard	WAVEGUDE AND METHOD OF FORMING THE OXIDE STRIFT HERE	OXIDE STRUCTURE USRABLE FOR OPTICAL WAYEGUIDE AND METHOD OF FORMING THE	OXIDE STRUCTURE USEABLE ROP OPTICAT	WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE MACEUM	DEPOSITION OF LOW STRESS GERMANIUM AND BORON DOPED SILICA BELLY SECTOR	WAVEGUIDES/Mognard	BELLOWS ROTARY PRED-THROUGH SEAL/ HE	AN IMPROVED DESIGN FOR A LINEAR INJECTOR ASSEMBLY/Mattern; Hakimelahy; Bartholomer- Pa-t-	Tun De Arroyana	DISTRIBUTION SYSTEM Matteon; Hakimelahy;	DESIGN FOR A LINEAR INTECTOR ASSEMBLY/	DESIGN FOR A LINEAR INTECTOR ASSEMBLY	PROTECTIVE SHIRLD AND SYSTEM FOR GAS	DISTRIBUTION/Mattson; Haldmelahy; Bartholomew;	ATMOSPHERIC PRESSURE WAFER PROCESSING REACTOR HAVING AN INTERNAL PRESSURE	CONTROL SYSTEM AND METHOD/Bartholomew;	
			Med		MSS	MSS		N N N	KBG KBG	SS HL	MSS	MSS		NESS MBG	j	1	- 1	MESS		
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			Ļ	CONTROL SYSTEM AND METHOD/Bartholomew.	Filling Date	Istue Date	Foreign Countries	
FA	70896	Se Mrry	MSS	ATMOSPHERIC PRESTIBE WITH		:.		Ì
		· · · · · · · · · · · · · · · · · · ·	WBG	REACTOR HAVING AN INTERNAL PROCESSING CONTROL SYSTEM AND METHOD/Bartholomew.	PI20023123 08/23/02		Malaysia	
FA	70896	96 TW	MSS	ATMOSPHERIC PRESSURE WAPER PROTESSION			,	-
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匙	70896	) 2: 9	MSS	ATMOSPHERIC PRESSURE WARTE PROGRESSION				
			•	REACTOR HAVING AN INTERNAL PRESSURE CONTROL SYSTEM AND METHODIA: #6/	PCT/US02/27372 08/26/02		PCT	·
Д,	71033	5	NESS	APPARATUS AND PROCESS FOR IMPROVED THEIR				
∢	71033	_	MSS	SYSTEM AND METHOD FOR IMPROVED THEN	60/332,397 11/16/01	Closed		<del></del>
Æ	71033	3	MSS	SYNTEM AND METHOD FOR IMPROVED THEIR	10/106,677 03/25/02			
FA	71033	R	S		02157580.0 11/15/02		Sign of the second	
Æ	71033	Ħ.	NESS IN		2002-333209 11/18/02		Japan	
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			·		Diel. HCIRIC FILMS/Seazald; Hering; Helins; Osbome	Closed			T
<del>'</del>		267 267		MSS	OPTIMIZATION OF CHEMICAL REACTION RATE	700		·.	
					COMPUTER STAULONATED ITERATIVE				T
					APPROACHION USING A DESIGNED-EXPERIMENT	·. ·			<del>-</del>
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<u>∢</u>		71181		MSS	HEATED VACUUM SIPPORT AREA IN THE	11/26/01			
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₹		71181	MY.	NISS	TED VACUUM SUPPORT APPARTING Kenn	11/22/02			<del></del> -
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駐	T	711817	2	Mes		31124187 11/25/02		Taiwan .	<del>-</del> i-
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·			•	TIH	IN-SITU CLEANING METHOD/Harring Steem	10/318,664			
¥.	Γ	71197 IMV	T	Neo		12/12/02			
				3	AND IN-SITU CLEANING METHOD/Haming, SILLING	PI 20031610		Med	
¥	Γ	71197 TW.	T	MSS		04/29/03		BIRKEN	
					AND IN-SITU CLEANING METHOD/Harring: Sisson;	92110202		Taiwan	
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WD. & ATOMIC LAYER DEPOSITION OF HF-O H-Si-O-N FOR GATE AND CAPACITOR BCTRICS/Senzaki; Sang-in Loe WD. & ATOMIC LAYER DEPOSITION OF HF-O H-Si-O-N FOR GATE AND CAPACITOR BCTRICS/Senzaki; Sang-in Loe WD. & ATOMIC LAYER DEPOSITION OF HF-O H-Si-O-N FOR GATE AND CAPACITOR BCTRICS/Senzaki; Sang-in Loe WD. & ATOMIC LAYER DEPOSITION OF HF-O- H-Si-O-N FOR GATE AND CAPACITOR H-Si-O-N FOR GATE AND CAPACITOR H-Si-O-N FOR GATE AND CAPACITOR H-Si-O-N FOR GATE AND CAPACITOR H-Si-O-N FOR GATE AND CAPACITOR H-Si-O-N FOR GATE AND CAPACITOR H-Si-O-N FOR GATE AND CAPACITOR H-Si-O-N FOR GATE AND CAPACITOR H-SI-O-N FOR GATE AND CAPACITOR H-SI-O-N FOR GATE AND CAPACITOR H-SI-O-N FOR GATE AND CAPACITOR H-SI-O-N FOR GATE AND CAPACITOR H-SI-O-N FOR GATE AND CAPACITOR H-SI-O-N FOR GATE AND CAPACITOR H-SI-O-N FOR GATE AND CAPACITOR H-SI-O-N FOR GATE AND CAPACITOR DIELECTRIC WITH WHED BLECTRICAL PROPERTIES/Senzahi:	60/394,744 07/19/02 07/17/03 07/16/03
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VD & ATOMIC LAYER DEPOSITION OF HE-O- If-SI-O-N FOR GAIE AND CAPACITOR ECTRICS/Senzaki; Sang-in Loo VD & ATOMIC LAYER DEPOSITION OF HE-O- If-SI-O-N FOR GAIE AND CAPACITOR If-SI-O-N FOR GAIE AND CAPACITOR ICAL UV. ASSISTED ATOMIC LAYER SITION/Senzaki; Sang-in Loo M OXIDATION FOR THE FORMATION OF GAIE AND CAPACITOR DIELECTRIC WITH VWED HIECTRICAL PROPERTIES/Senzaki	92119583 07/17/03 07/16/03
VD & ATOMIC LAYER DEPOSITION OF HE-O- IC-SI-O-N FOR GATE AND CAPACITOR SCTRICS/Senzali; Sang-in Lee TUM UV. ASSISTED ATOMIC LAYER SITION/Senzali; Sang-in Lee W OXIDATION FOR THE FORMATION OF GATE AND CAPACITOR DIELECTRIC WITH	07/16/03
TUM UV. ASSISTED ATOMIC LAYER STITON/Semaki; Sang-in Lee A OXIDATION FOR THE FORMATION OF GATE AND CAPACITOR DIELECTRIC WITH VVED BLECTRICAL PROPERTIES/Semaki:	
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д	71644		MSS	IN-SITU FORMATION OF MIM CAPACITORS/Sume-in Action 201	Filling Date	Internation	Foreign Countries	
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Title/Inventors	LOAD PORT APPARATUS; Jeffery B. Kowalahi	THERMAL PROCESSING CHAMBER ENVIRONMENTAL CONTROL SYSTEM AND METHOD: Alm Spring	CONTROL OF A GASEOUS ENVIRONMENT IN A WAFER LOADING CHAMBER; Alan Stemen	CONTROL OF A GASEOUS ENVIRONMENT IN A WAPER LOADING CHAMBER; Alen Steinet	METHOD AND SYSTEM FOR ISOTHERMAL HEATING OF WAFERS; Jefffey Kowalski	HEATER ELEMENT SELECTABLE FOR VARIABLE TEMPERATURE PROCESSING/Out	VARIABLE HEATER ELEMENT FOR LOW TO HIGH TEMPERATURE RANGES/Om	VARIABLE HEATER ELEMENT FOR LOW TO HIGH TEMPERATURE RANGES/Om	T-RAIL SUPPORT/DuBois	METHOD & APPARATUS FOR SUPPORTING SEMICONDUCTOR WAPPER SUPPORTING	RTING	FEED FORWARD CONTROL SYSTEM AND METHOD/Torkemen; Radiiff (This case may be related to A-71754)	SYSTEM ARCHITECTIBE AND METERS
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Ref	Reference No							
		·		Title/Inventors	_	Patent No.		ŀ
<u>A</u>	71824	_	MESS	REMOTE PLASMA NITRIDATION OF TIME & C.	-+	Isrue Date	Countries	
		•		DIRLECTRICX/Senzaki; Bercaw; Chafham; Higushi;	60/424,891 11/08/02		<i>c.</i>	1
∢	71824		MSS	REMOTS PLASMA NITRIDATION OF HIGH-K GATE DIST. BCTRICS/Senzaki; Bereav; Chatham; High-K GATE				
⋖	71884		MSSS TTH	METHOD OF ATOMIC LAYER REMOVAL OR BURACHINGS.mo.;h I	Closed, combined		:	
ρ,	72081		MSS	TRANSPORT SYSTEM HAVING SHAPED TO AD	with 71606			
	70138			ě .	60/443,969 01/31/03			T
			S	ELECTRODE STRUCTURE AND METHOD OF FABRICATING AN ELECTRODE HAVING LOW TEMPERATURE OXIDS FILM; S.I. Los, Y. Seizek		•	Client Red No D-7031	
. م	72218		MSS		60/464,458		Chart D. 6 M	
	7.35	**************************************		B CHE GAS DELIVERY MANIFOLD;	04/21/03		D-2419	
4	72332		MSS	Day of the second	053000	The recommendation of China Bucho.	Gient Ref. No. D-2493	<del>,                                     </del>
V	72333		MSS	METHOD OF REDUCING CONTACT PRESERVANCE				
V	72344		MSS	OF COPPER INTERCONNECT				<u> </u>
		·	,	TEMPERATURE CONTROL USING A BOTTOM AND	12			
<	72345	4	MSS	SEMICONDUCTOR VERTICAL FURNACE HALO RING CONCEPT, D. DuBois, C. Potter, M. Morsen				
<u> </u>	†	1	].					•

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Patient No./ Isone Date	
Serial No./ Filing Date	
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Title/Inventors	
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Reference Nos:
"A," denotes US a patent/patent application/invention disclosure
"FA" "FP" and "FE" denote a. foreign patent/patent application